

L Number	Hits	Search Text	DB	Time stamp
1	26	5676587.pn. 5853604.uref. 5827781.uref.	USPAT; US-PGPUB	2003/03/06 11:00
2	2	5853604.pn. 5827781.pn.	USPAT; US-PGPUB	2003/03/06 11:20
3	5	("4193226"   "4811522"   "4963283"   "5391258"   "5421769").PN.	USPAT	2003/03/06 11:02
4	5	("3691694"   "5081421"   "5536202"   "5643405"   "5733177").PN.	USPAT	2003/03/06 11:03
5	8	5733177.uref.	USPAT; US-PGPUB	2003/03/06 11:40
6	5101	438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.	USPAT; US-PGPUB	2003/03/06 11:42
7	210	(438/626.ccls. 438/633.ccls. 438/687.ccls.) and (438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.)	USPAT; US-PGPUB	2003/03/06 11:43
8	389	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and (relative near2 (speed velocity))	USPAT; US-PGPUB	2003/03/06 11:49
10	2041	((cmp (chemical near mechanical)) with (copper cu conduct\$4 metal))	EPO; JPO; DERWENT; IBM_TDB	2003/03/06 11:50
12	8908	((cmp (chemical near mechanical)) with (copper cu conduct\$4 metal))	USPAT; US-PGPUB	2003/03/06 11:51
13	8	((cmp (chemical near mechanical)) with (copper cu conduct\$4 metal)) same (relative near2 (speed velocity))	USPAT; US-PGPUB	2003/03/06 14:14
9	93	((438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and (relative near2 (speed velocity))) and ((cmp (chemical near mechanical)) with (copper cu conduct\$4 metal))	USPAT; US-PGPUB	2003/03/06 12:04
14	2	((438/626.ccls. 438/633.ccls. 438/687.ccls.) and (438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.)) and (relative near2 (speed velocity))	USPAT; US-PGPUB	2003/03/06 14:13
15	14	((cmp (chemical near mechanical)) with (copper cu conduct\$4 metal)) same ((relative linear) near2 (speed velocity))	USPAT; US-PGPUB	2003/03/06 14:21
16	16	((cmp (chemical near mechanical)) with (copper cu conduct\$4 metal)) same ((rotat\$6 near2 (speed velocity)) rpm rpms) same (change decreas\$4 reduc\$5)	USPAT; US-PGPUB	2003/03/06 14:23
11	3	((cmp (chemical near mechanical)) with (copper cu conduct\$4 metal)) and (relative near2 (speed velocity))	EPO; JPO; DERWENT; IBM_TDB	2003/03/06 14:38
17	1888	(cmp (chemical near mechanical) polish\$4) and ((carrier head) same (retain\$4 ring membrane)) and (wafer substrate) and (platen pad)	USPAT; US-PGPUB	2003/03/06 15:02
18	505	(cmp (chemical near mechanical) polish\$4) and ((carrier head) same (retain\$4 ring membrane) same (platen pad) same (pressure psi pa)) and (wafer substrate)	USPAT; US-PGPUB	2003/03/06 15:03
19	501	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and ((cmp (chemical near mechanical) polish\$4) and ((carrier head) same (retain\$4 ring membrane)) and (wafer substrate) and (platen pad))	USPAT; US-PGPUB	2003/03/06 14:49
20	203	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and ((cmp (chemical near mechanical) polish\$4) and ((carrier head) same (retain\$4 ring membrane) same (platen pad) same (pressure psi pa)) and (wafer substrate))	USPAT; US-PGPUB	2003/03/06 14:49

22	787	((cmp (chemical near mechanical) polish\$4) with (copper cu conduct\$4 metal)) and ((carrier head) same (retain\$4 ring membrane)) and (wafer substrate) and (platen pad)	USPAT; US-PGPUB	2003/03/06 14:54
23	231	((cmp (chemical near mechanical) polish\$4) with (copper cu conduct\$4 metal)) and ((carrier head) same (retain\$4 ring membrane) same (platen pad) same (pressure psi pa)) and (wafer substrate)	USPAT; US-PGPUB	2003/03/06 14:57
25	249	(cmp (chemical near mechanical) polish\$4) and ((carrier head) same (retain\$4 ring membrane)) and (platen pad)	EPO; JPO; DERWENT; IBM_TDB	2003/03/06 15:02
21	83	(cmp (chemical near mechanical) polish\$4) and ((carrier head) same (retain\$4 ring) same membrane same (platen pad) same (pressure psi pa)) and (wafer substrate)	USPAT; US-PGPUB	2003/03/06 15:04
24	112	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and (((cmp (chemical near mechanical) polish\$4) with (copper cu conduct\$4 metal)) and ((carrier head) same (retain\$4 ring membrane) same (platen pad) same (pressure psi pa)) and (wafer substrate))	USPAT; US-PGPUB	2003/03/06 16:00
27	111	((cmp (chemical near mechanical) polish\$4) and ((carrier head) same (retain\$4 ring membrane)) and (platen pad)) and (pressure psi pa copper cu metal conduct\$4)	EPO; JPO; DERWENT; IBM_TDB	2003/03/06 17:01
-	1	6204181.pn.	USPAT; US-PGPUB	2003/03/06 09:48
-	1	20010004538.pn.	USPAT; US-PGPUB	2003/03/05 17:55